

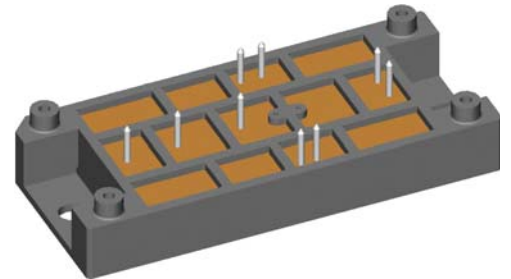
Standard Rectifier Module

3~ Rectifier
$V_{RRM} = 1200\text{ V}$
$I_{DAV} = 180\text{ A}$
$I_{FSM} = 1100\text{ A}$

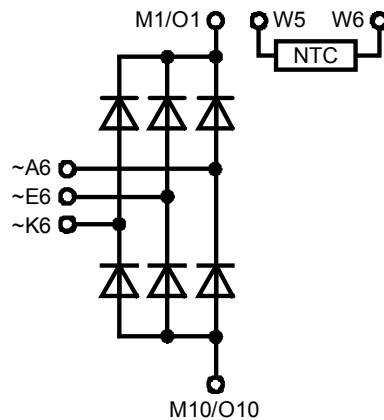
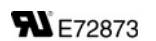
3~ Rectifier Bridge + NTC

Part number

VUO120-12NO2T



Backside: isolated



Features / Advantages:

- Package with DCB ceramic
- Reduced weight
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current
- NTC

Applications:

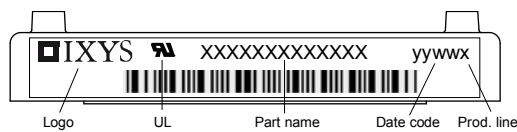
- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: V2-Pack

- Isolation Voltage: 3600V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 17 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V	
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
I_R	reverse current	$V_R = 1200 V$	$T_{VJ} = 25^{\circ}C$		100	μA	
		$V_R = 1200 V$	$T_{VJ} = 125^{\circ}C$		2	mA	
V_F	forward voltage drop	$I_F = 60 A$	$T_{VJ} = 25^{\circ}C$		1.16	V	
		$I_F = 180 A$			1.55	V	
		$I_F = 60 A$	$T_{VJ} = 125^{\circ}C$		1.09	V	
		$I_F = 180 A$			1.59	V	
I_{DAV}	bridge output current	$T_C = 90^{\circ}C$ rectangular $d = 1/3$	$T_{VJ} = 150^{\circ}C$		180	A	
V_{FO}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0.81	V	
r_F	slope resistance				4.4	m Ω	
R_{thJC}	thermal resistance junction to case				0.6	K/W	
R_{thCH}	thermal resistance case to heatsink			0.2		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		205	W	
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		1.10	kA	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		1.19	kA	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		935	A	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		1.01	kA	
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		6.05	kA ² s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		5.89	kA ² s	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		4.37	kA ² s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		4.25	kA ² s	
C_J	junction capacitance	$V_R = 400 V; f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		37	pF	

Package V2-Pack			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{stg}	storage temperature		-40		125	°C
T_{VJ}	virtual junction temperature		-40		150	°C
Weight				76		g
M_D	mounting torque		2		2.5	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3000			V



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO120-12NO2T	VUO120-12NO2T	Box	6	510989

Similar Part	Package	Voltage class
VUO120-16NO2T	V2-Pack	1600

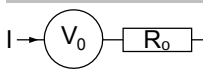
Temperature Sensor NTC

Symbol	Definition	Conditions	min.	typ.	max.	Unit
R_{25}	resistance	$T_{VJ} = 25^\circ$	4.75	5	5.25	k Ω
$B_{25/50}$	temperature coefficient			3375		K

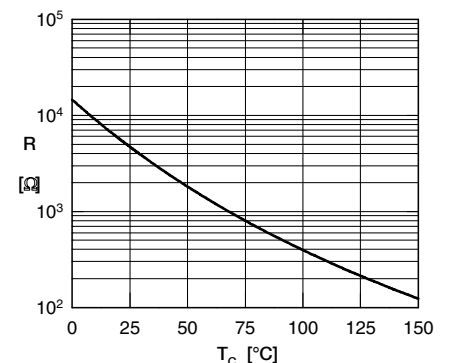
Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^\circ\text{C}$



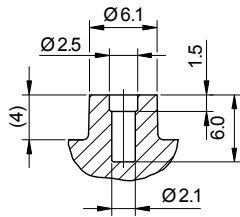
$V_{0\max}$	threshold voltage	0.81				V
$R_{0\max}$	slope resistance *	3.2				m Ω



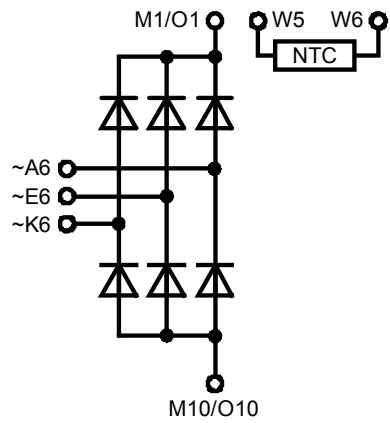
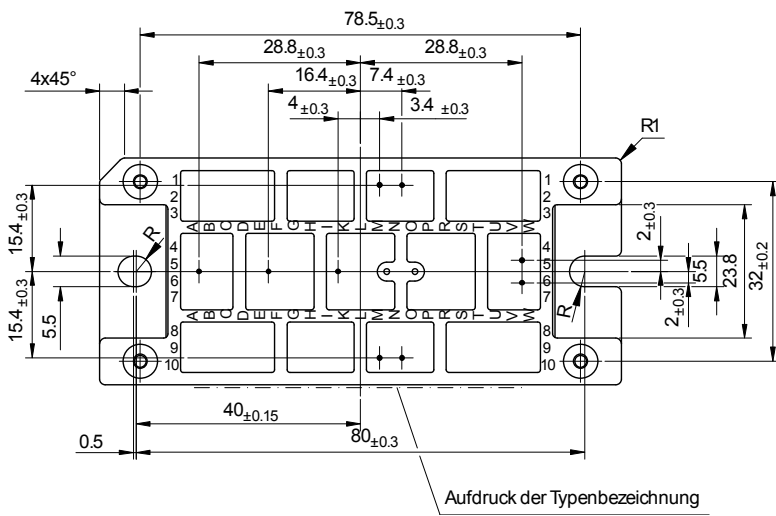
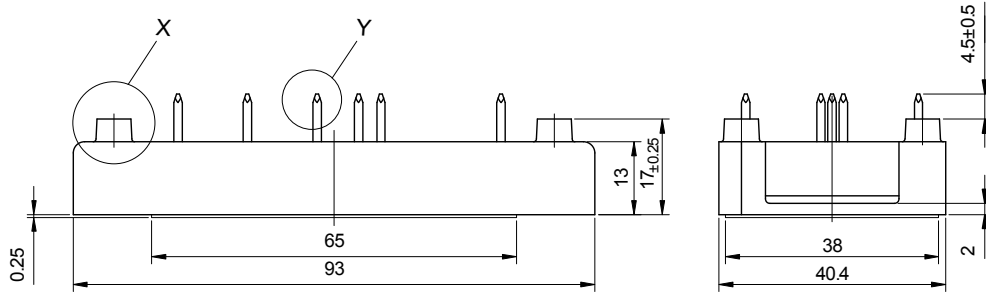
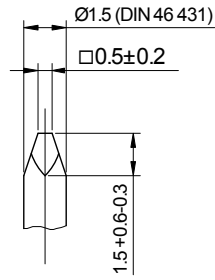
Typ. NTC resistance vs. temperature

Outlines V2-Pack

Detail X M2:1



Detail Y M5:1



Rectifier

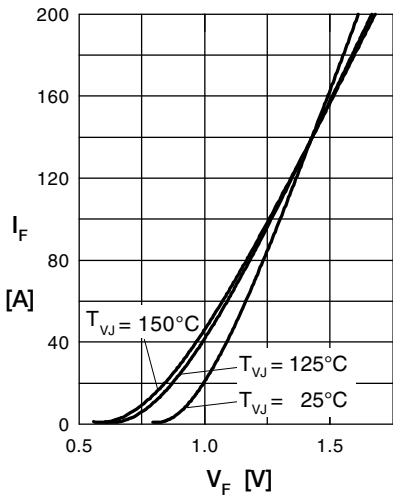


Fig. 1 Forward current vs. voltage drop per diode

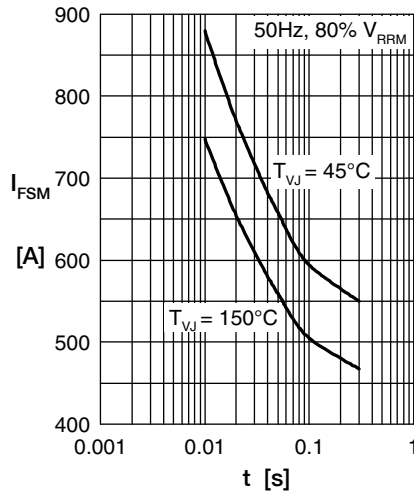


Fig. 2 Surge overload current vs. time per diode

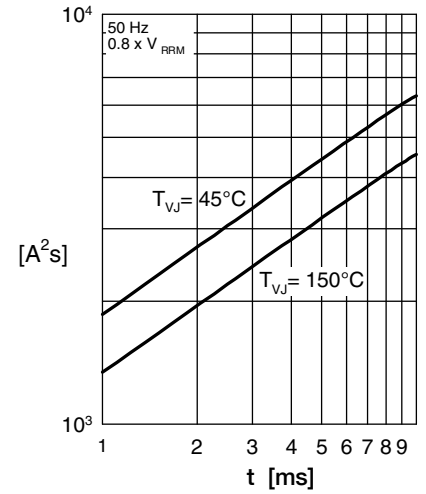


Fig. 3 I^2t vs. time per diode

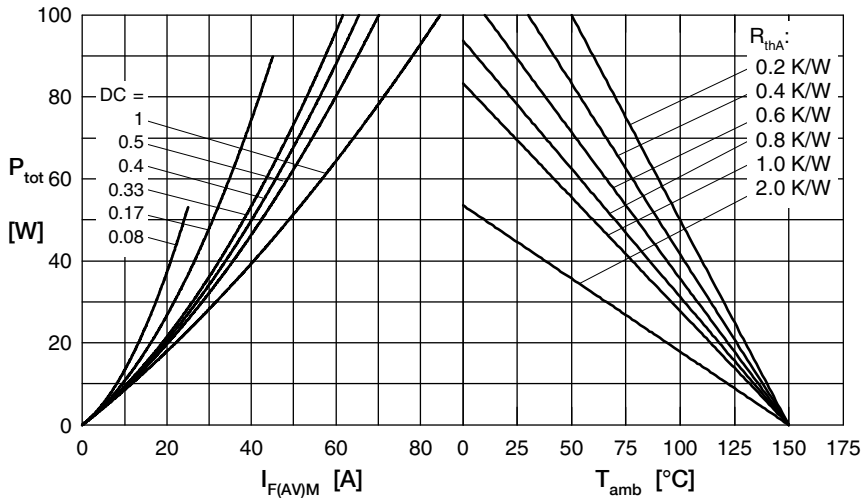


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

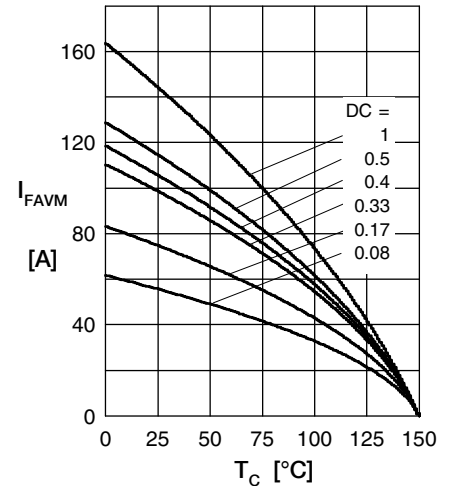


Fig. 5 Max. forward current vs. case temperature per diode

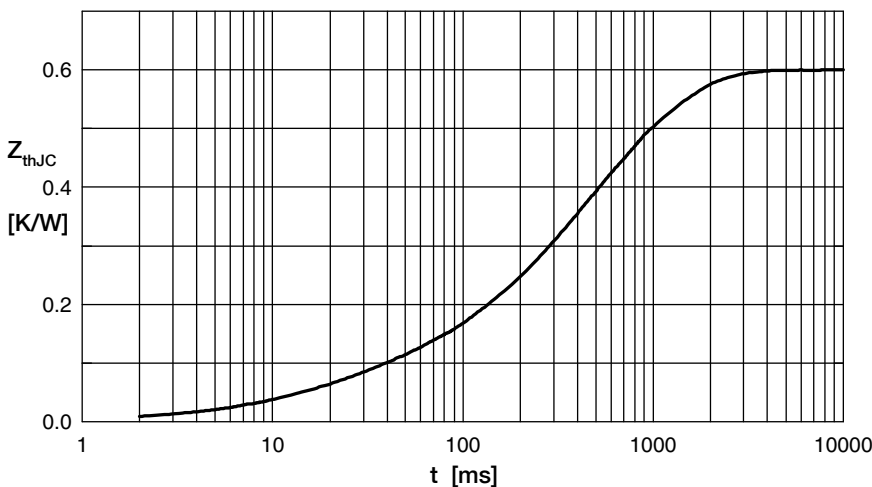


Fig. 6 Transient thermal impedance junction to case vs. time per diode

R_i	t_i
0.060	0.020
0.003	0.010
0.150	0.225
0.243	0.800
0.144	0.580